



**THE DATASHEET OF
C3D10060G-TR**



C3D10060G

600 V, 10 A Silicon Carbide Schottky Diode



TO-263-2



Features

- 600-Volt Schottky rectifier
- Zero reverse recovery current
- Zero forward recovery voltage
- High-frequency operation
- Temperature-independent switching behavior
- Extremely fast switching
- Positive temperature coefficient on V_f



Package Types: TO-263-2

PN: C3D10060G

WolfSpeed, Inc. is in the process of rebranding its products and related materials pursuant to the entity name change from Cree, Inc. to WolfSpeed, Inc. During this transition period, products received may be marked with either the Cree name and/or logo or the WolfSpeed name and/or logo.

Applications

- Switch mode power supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free wheeling diodes in inverter stages
- AC/DC converters

Benefits

- Replace bipolar with unipolar rectifiers
- Essentially no switching losses
- Higher efficiency
- Reduction of heat sink requirements
- Parallel devices without thermal runaway

Maximum Ratings ($T_c = 25\text{ }^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note
Repetitive Peak Reverse Voltage	V_{RRM}	600	V		
Surge Peak Reverse Voltage	V_{RSM}	600			
DC Blocking Voltage	V_{DC}	600			
Continuous Forward Current	I_F	29	A	$T_c = 25\text{ }^\circ\text{C}$	Fig. 3
		14		$T_c = 135\text{ }^\circ\text{C}$	
		10		$T_c = 151\text{ }^\circ\text{C}$	
Repetitive Peak Forward Surge Current	I_{FRM}	44	A	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	Fig. 8
		30.5		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	90	A	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	Fig. 8
		71		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	
Non-Repetitive Peak Forward Surge Current	$I_{F,Max}$	860	A	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ }\mu\text{s}$, Pulse	Fig. 8
		680		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ }\mu\text{s}$, Pulse	
Power Dissipation	P_{tot}	125	W	$T_c = 25\text{ }^\circ\text{C}$	Fig. 4
		54		$T_c = 110\text{ }^\circ\text{C}$	
Diode dV/dt Ruggedness	dV/dt	200	V/ns	$V_R = 0\text{--}600\text{ V}$	
i^2t Value	$\int i^2 dt$	40.5	A^2s	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$	
		25		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$	
Operating Junction and Storage Temperature	$T_{J, T_{stg}}$	-55 to +175	$^\circ\text{C}$		



Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Note
Forward Voltage	V_F	1.5	1.8	V	$I_F = 10 \text{ A}, T_J = 25^\circ\text{C}$	Fig. 1
		2.0	2.4		$I_F = 10 \text{ A}, T_J = 175^\circ\text{C}$	
Reverse Current	I_R	10	50	μA	$V_R = 600 \text{ V}, T_J = 25^\circ\text{C}$	Fig. 2
		20	200		$V_R = 600 \text{ V}, T_J = 175^\circ\text{C}$	
Total Capacitive Charge	Q_C	24		nC	$V_R = 400 \text{ V}, I_F = 10 \text{ A}$ $di/dt = 500 \text{ A}/\mu\text{S}$ $T_J = 25^\circ\text{C}$	Fig. 5
Total Capacitance	C	460.5		pF	$V_R = 0 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	Fig. 6
		44			$V_R = 200 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	
		40			$V_R = 400 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E_C	3.6		μJ	$V_R = 400 \text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.2	$^\circ\text{C}/\text{W}$	Fig. 9

Typical Performance

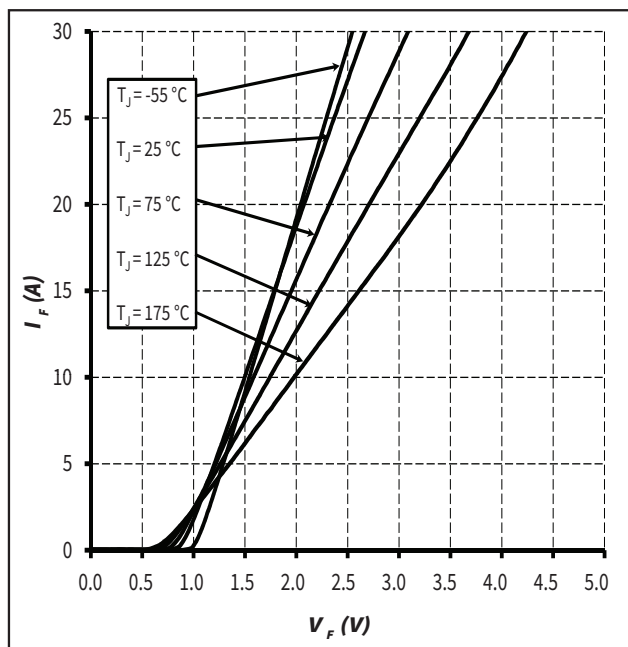


Figure 1. Forward Characteristics

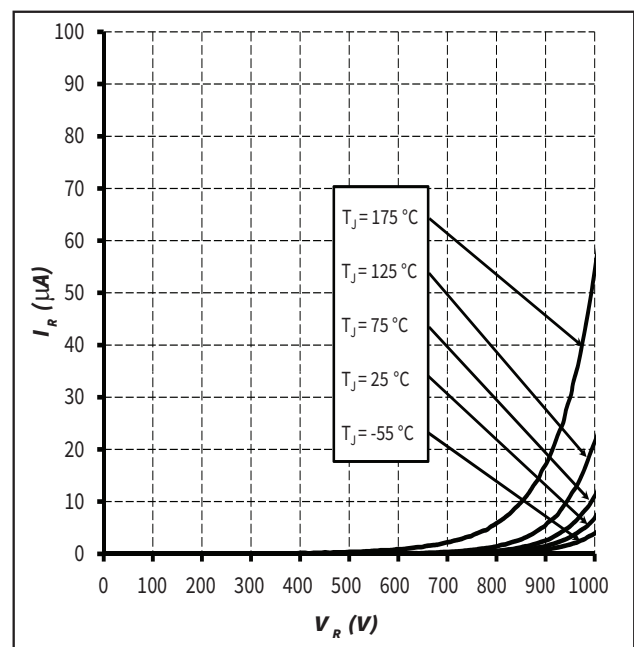


Figure 2. Reverse Characteristics



Typical Performance

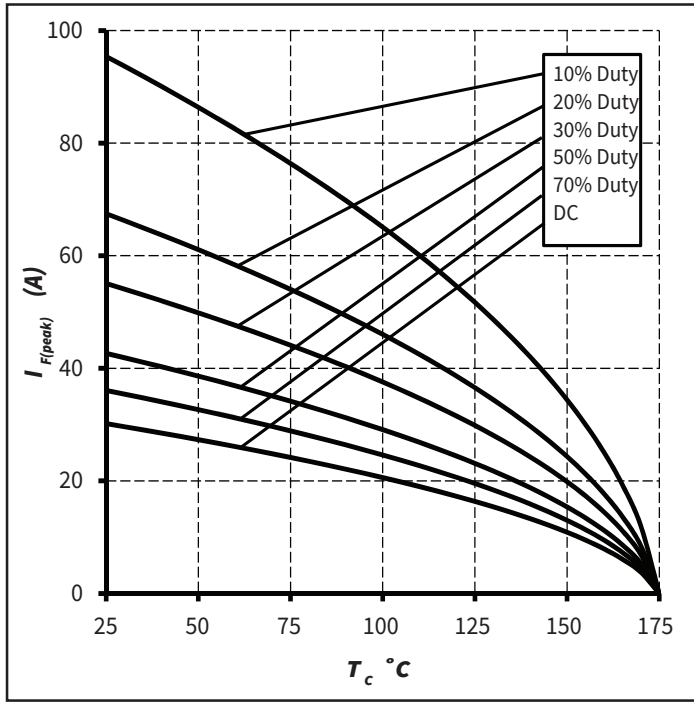


Figure 3. Current Derating

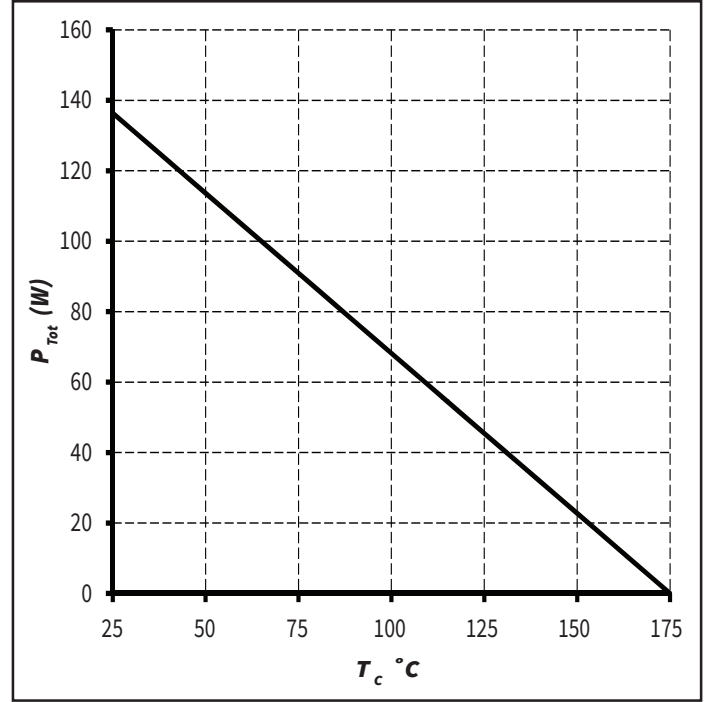


Figure 4. Power Derating

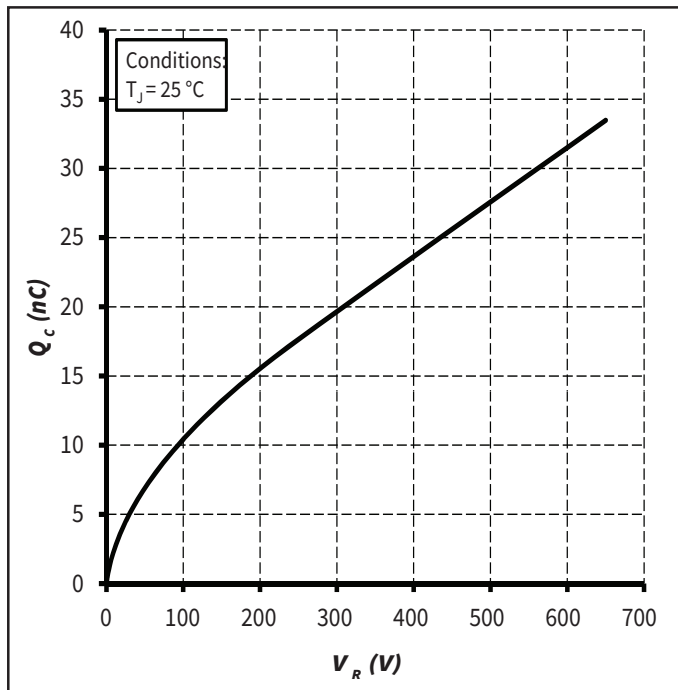


Figure 5. Total Capacitance Charge vs. Reverse Voltage

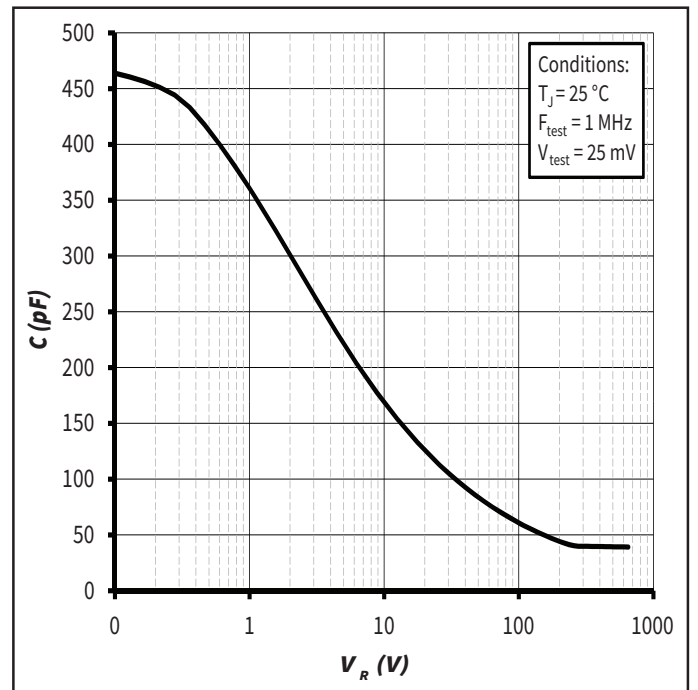


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance

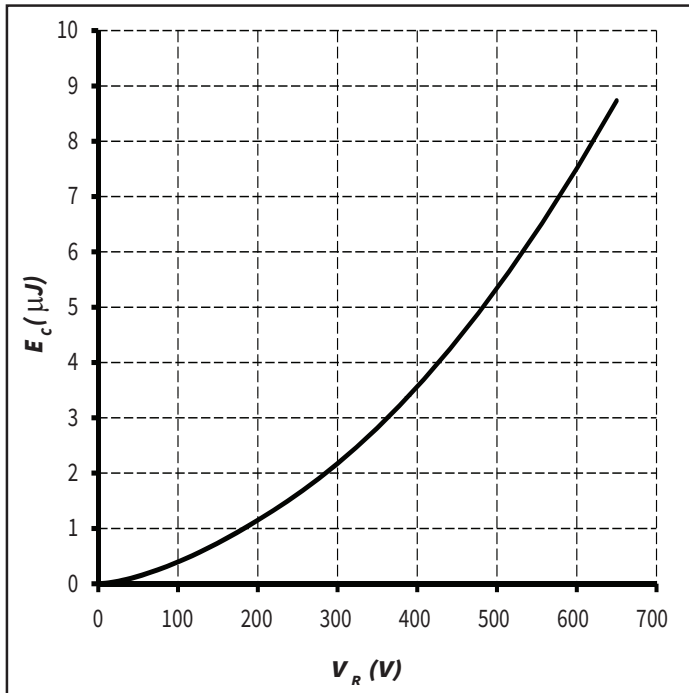


Figure 7. Capacitance Stored Energy

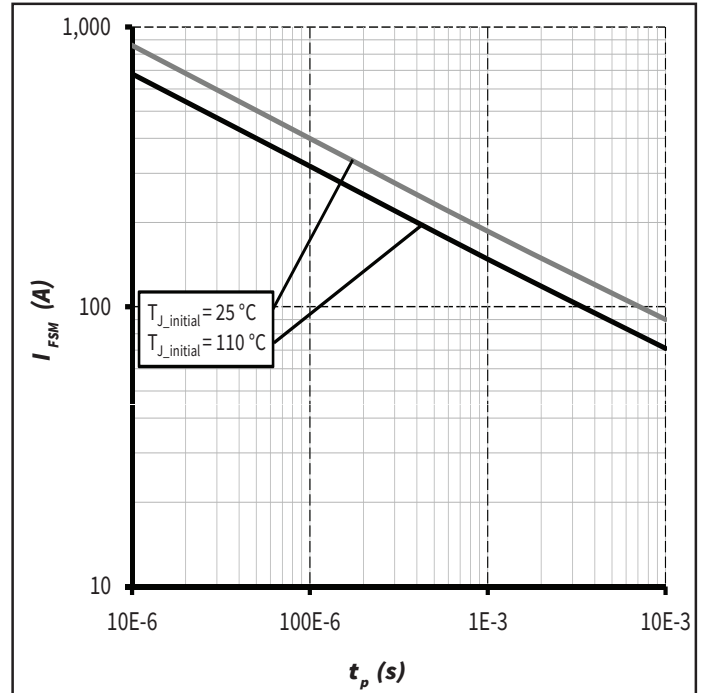


Figure 8. Non-Repetitive Peak Forward Surge Current Versus Pulse Duration (Sinusoidal Waveform)

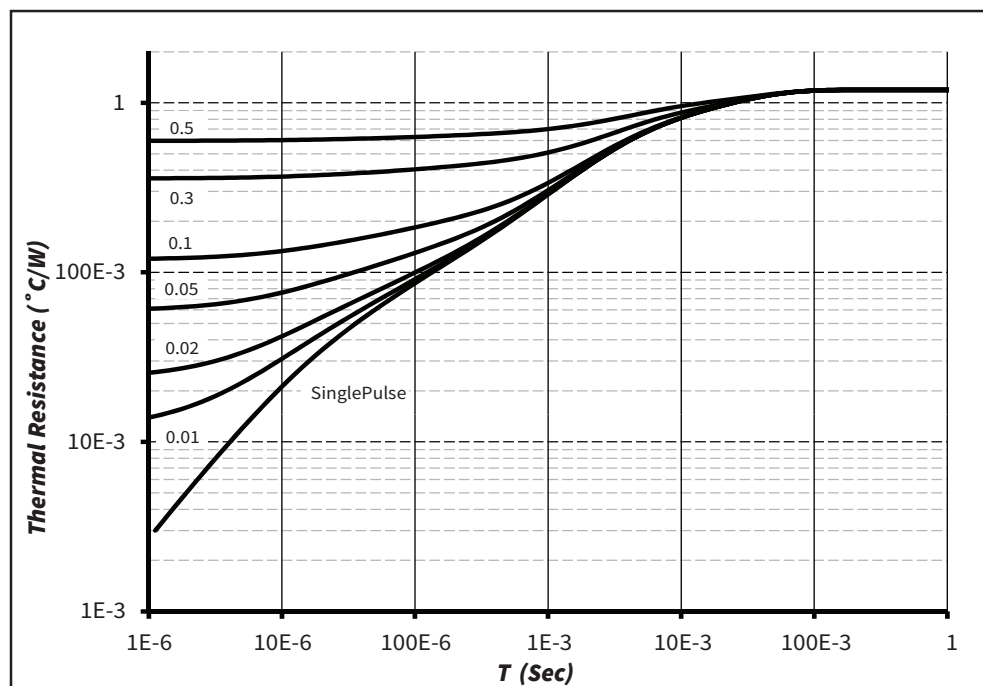
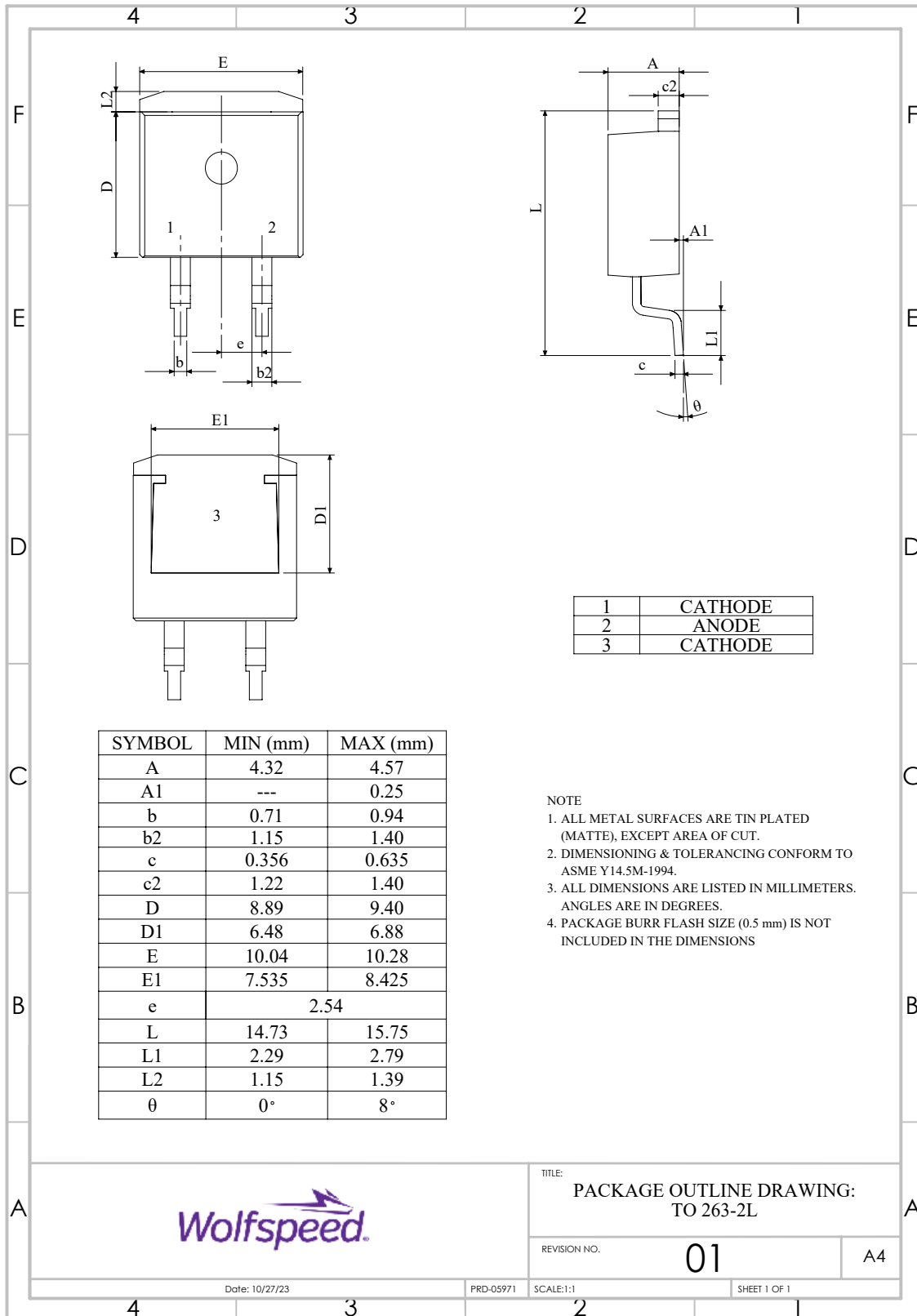


Figure 9. Transient Thermal Impedance

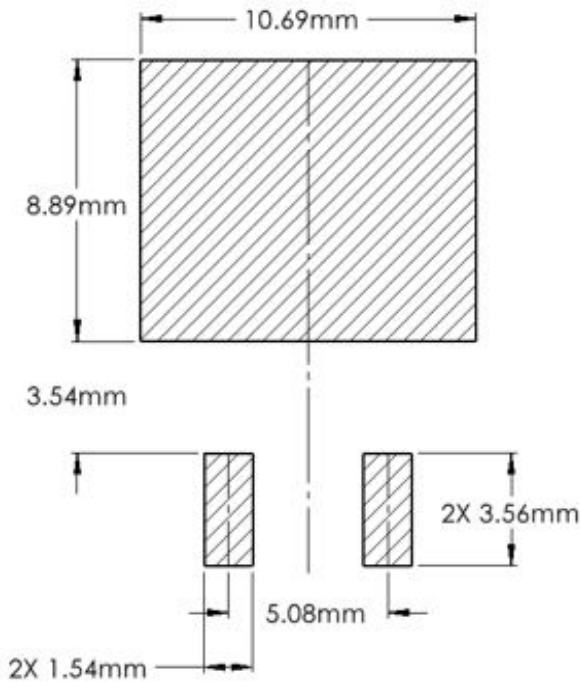


Package Dimensions

Package: TO-263-2

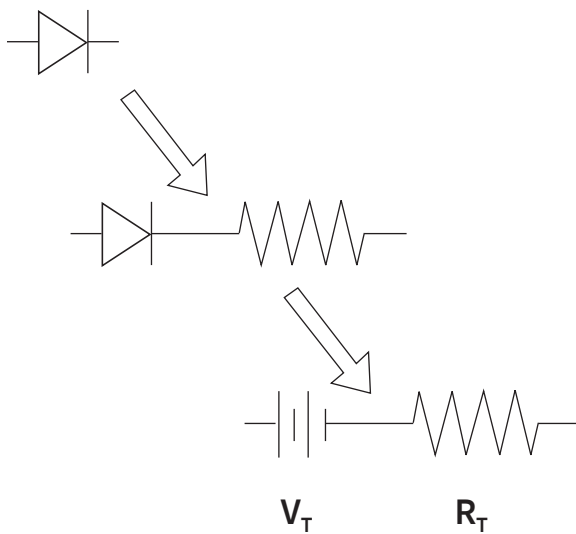


Recommended Solder Pad Layout



Part Number	Package	Marking
C3D10060G	TO-263-2	C3D10060

Diode Model



$$V_{f_T} = V_T + I_f \cdot R_T$$

$$V_T = 0.94 + (T_j \cdot -1.3 \cdot 10^{-3})$$

$$R_T = 0.044 + (T_j \cdot 4.4 \cdot 10^{-4})$$

Note: T_j = Diode Junction Temperature in Degrees Celsius,
Valid from 25 °C to 175 °C



Revision History

Current Revision	Date of Release	Description of Changes
H	January-2017	Initial Release
11	October-2023	Updated Wolfspeed branding, package drawing, package image, and solder pad layout (Not Released)
12	November-2023	Corrected Package Drawing L and L1



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